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IN THE CLAIMS:

Please amend the claims as follows:

1. – 3. (Cancelled)

4. (Currently amended) The method of claim 3, wherein A method of modulating the flatband voltage of a high-k dielectric material of a semiconductor device, comprising the steps of: depositing the high-k dielectric material on a surface; and controllably modulating the flatband voltage of the high-k dielectric material by annealing the high-k dielectric material under controlled annealing parameters, wherein:

the controlled annealing parameters include at least one of: annealing temperatures; annealing times; annealing gases; and number of anneals;
the annealing includes controlling the temperature of anneals about 400°C to about 1000°C; and

the annealing includes a plurality of anneals with a different annealing gas in each anneal.

5. (Original) The method of claim 4, wherein the annealing gases include at least one of: O₂, N₂, H₂ and NH₃.

6. (Original) The method of claim 5, wherein the annealing includes controlling the annealing time between 10 seconds to 60 seconds.

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7. (Currently amended) The method of claim 1-4, wherein the step of controlling modulating includes changing the flatband voltage by at least 0.3V.

8. (Currently amended) The method of claim 1-4, wherein the step of controllably modulating includes modulating the high-k dielectric material for P-channel devices to a first value and the high-k dielectric material for N-channel devices to a second value different from the first value.

9. (Currently amended) The method of claim 8, wherein A method of modulating the flatband voltage of a high-k dielectric material of a semiconductor device, comprising the steps of: depositing the high-k dielectric material on a surface; and controllably modulating the flatband voltage of the high-k dielectric material by annealing the high-k dielectric material under controlled annealing parameters, wherein the step of controllably modulating includes modulating the high-k dielectric material for P-channel devices to a first value and the high-k dielectric material for N-channel devices to a second value different from the first value, and the step of modulating the high-k dielectric material for P-channel devices to a first value includes annealing with N₂.

10. (Original) The method of claim 9, further comprising preventing exposure of the high-k dielectric material for N-channel devices to the N₂ during the step of modulating the high-k dielectric material for P-channel devices.

11. - 12. (Cancelled)

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13. (Currently amended) ~~The method of claim 12, wherein A method for forming a semiconductor chip, comprising the steps of:~~

depositing a high-k dielectric film;

annealing to modify the flatband voltage of the high-k dielectric film to a first value for a first set of devices on the chip; and

annealing to modify the flatband voltage of the high-k dielectric film to a second value, different than the first value, for a second set of devices on the chip, wherein:

the first set of devices are N-channel devices and the second set of devices are P-channel devices; and

the step of annealing to modify the flatband voltage of the high-k dielectric film includes masking the N-channel devices and subjecting the P-channel devices to annealing with N₂.

14. (Original) The method of claim 13, further comprising subjecting both the N-channel devices and the P-channel devices to an annealing with NH₃ and an annealing with O₂.

15. (Original) The method of claim 14, further comprising subjecting both the N-channel devices and the P-channel devices to an annealing with H₂.

16. (Original) The method of claim 15, further comprising controlling annealing temperature during each annealing to control the flatband voltage of the high-k dielectric film.

17. (Original) The method of claim 16, further comprising controlling annealing time during each annealing to control the flatband voltage of the high-k dielectric film.